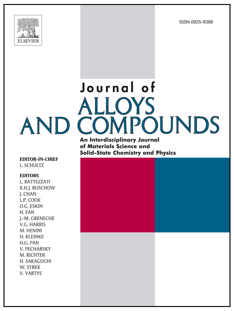

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PII: S0925-8388(16)32760-8

DOI: 10.1016/j.jallcom.2016.09.028

Reference: JALCOM 38862

To appear in: *Journal of Alloys and Compounds*

Received Date: 13 January 2016

Revised Date: 2 September 2016

Accepted Date: 3 September 2016

Please cite this article as: H. Saïdi, M.F. Boujmil, B. Durand, M. Bouaïcha, Physical properties of highly crystalline CIS layer prepared using single phase electrodeposition and low temperature RTP annealing, *Journal of Alloys and Compounds* (2016), doi: 10.1016/j.jallcom.2016.09.028.

Graphical abstract